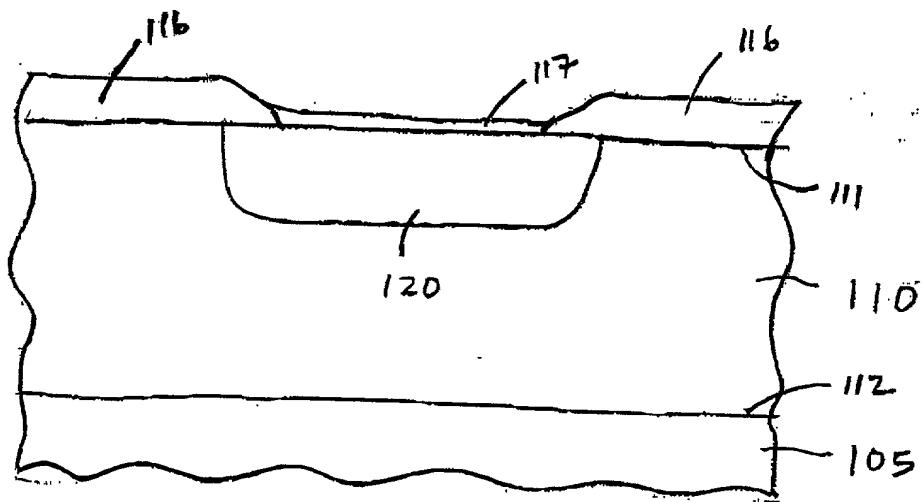
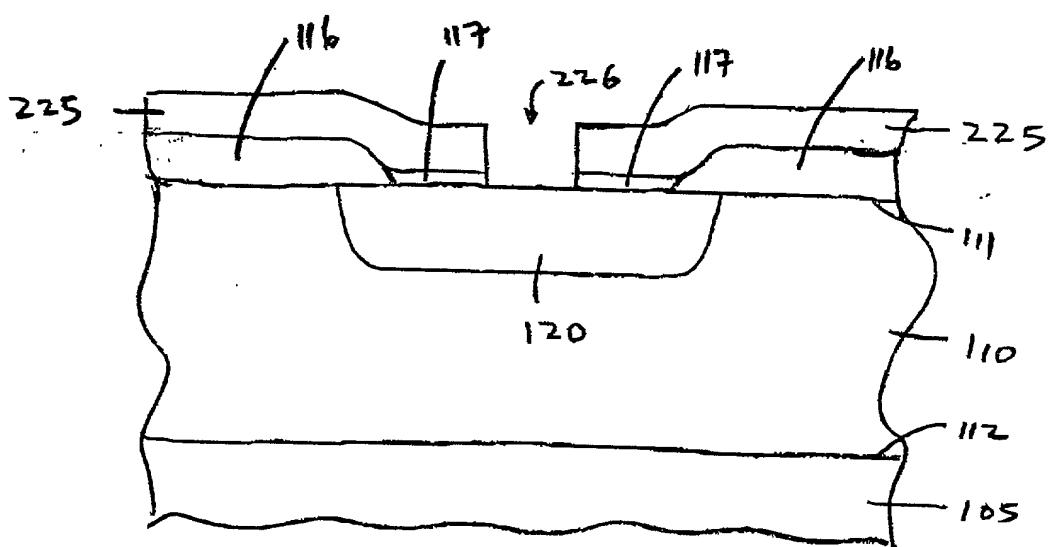


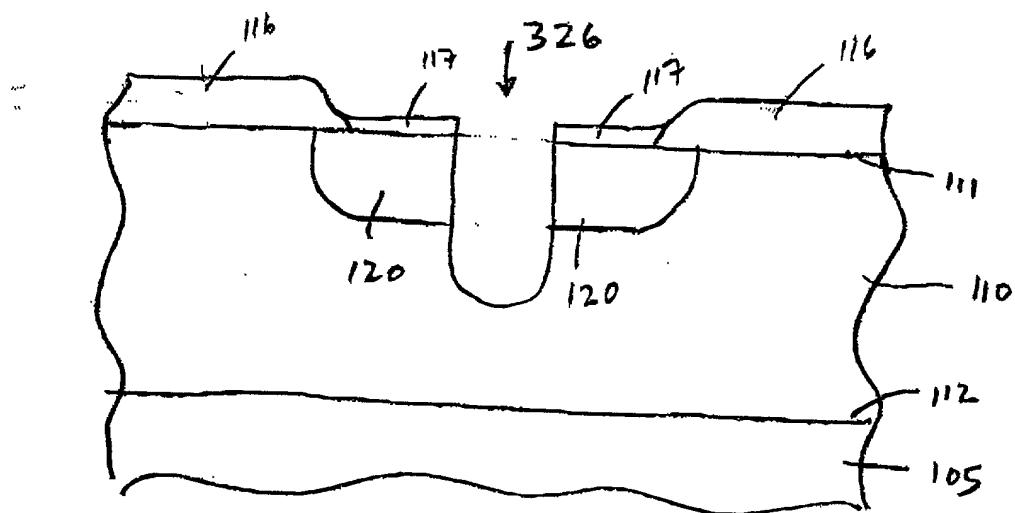
0003027285 - 00342004



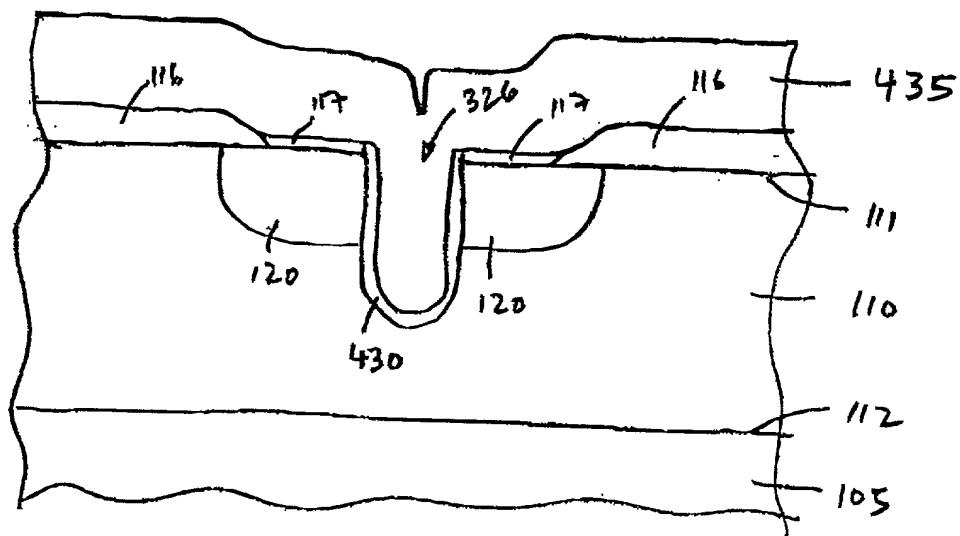
100
FIG. 1



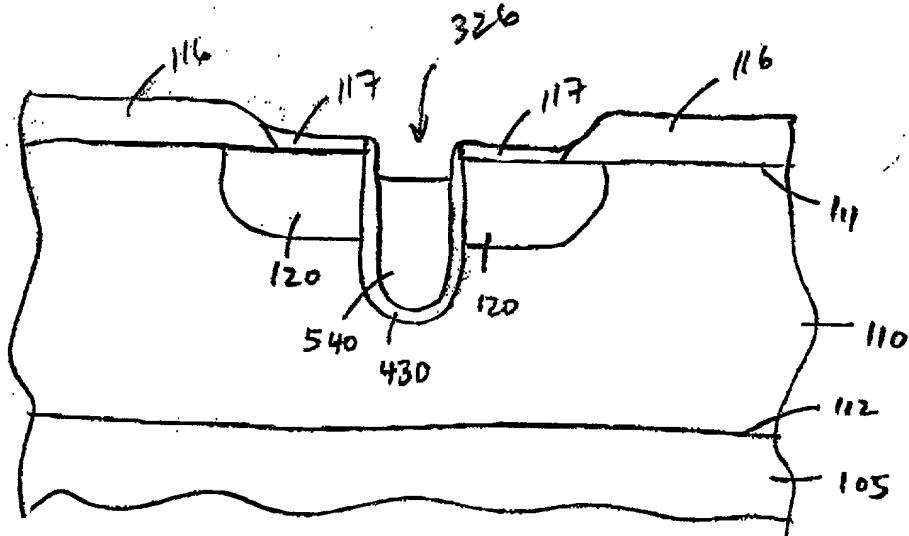
100
FIG. 2



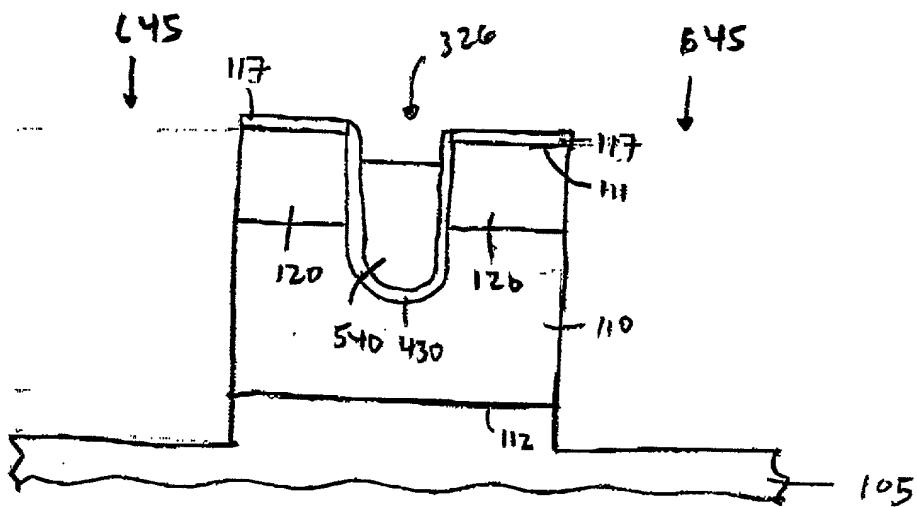
100
FIG. 3



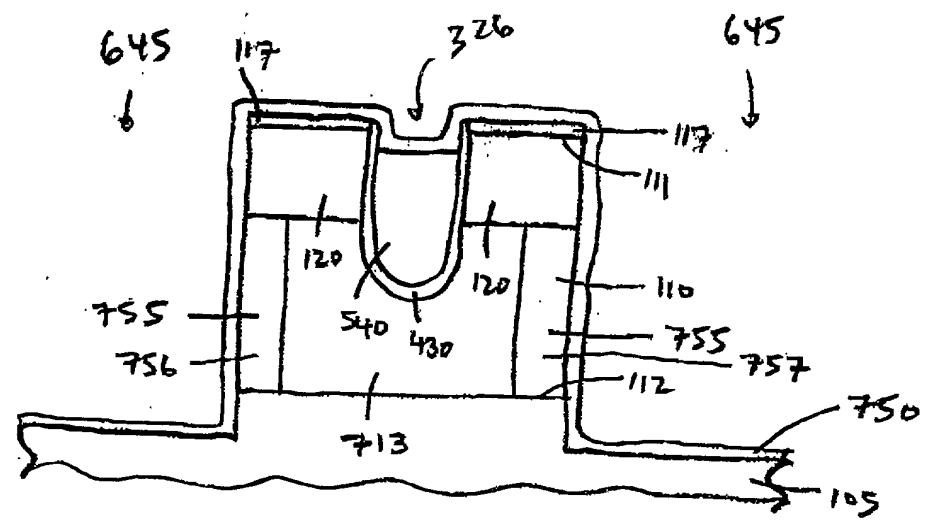
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FIG. 4



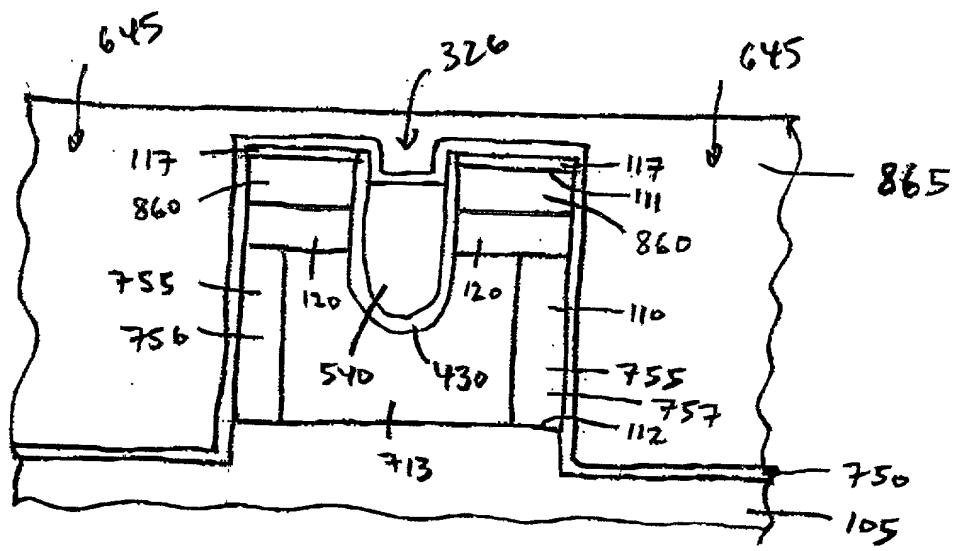
100
FIG. 5



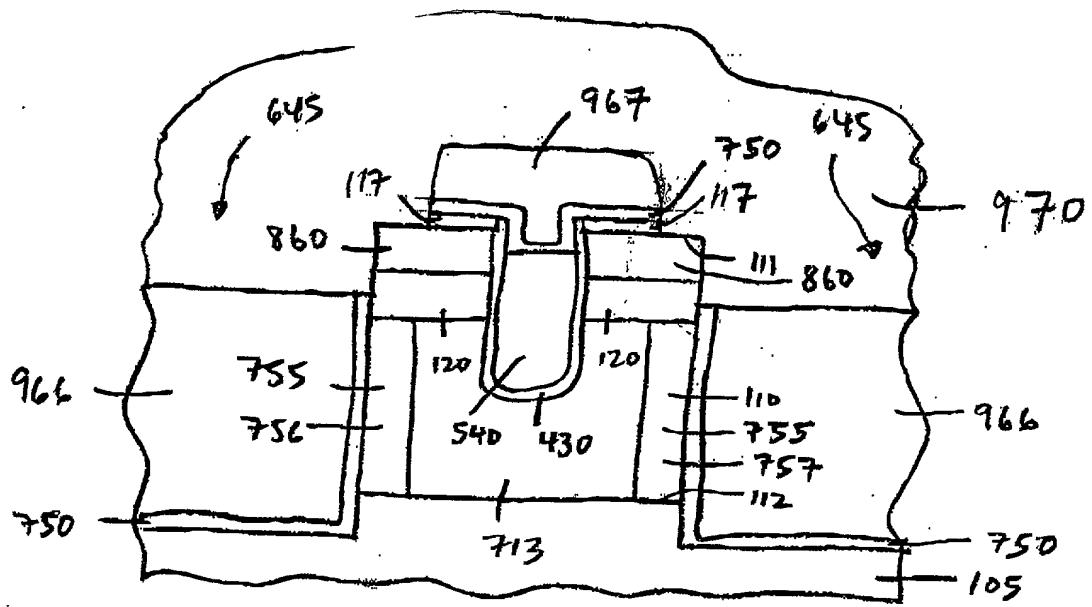
100
FIG. 6



100
FIG. 7

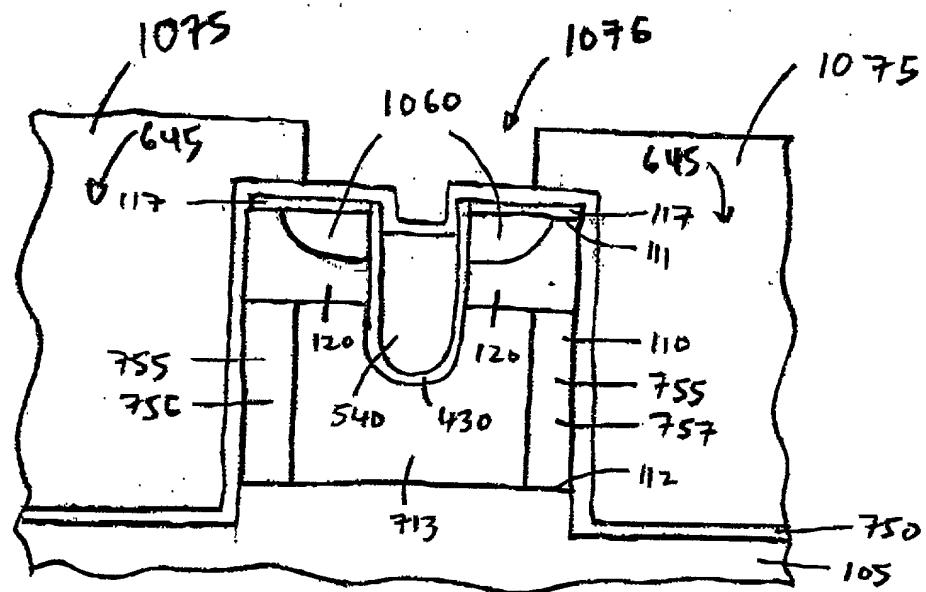


100
FIG. 8



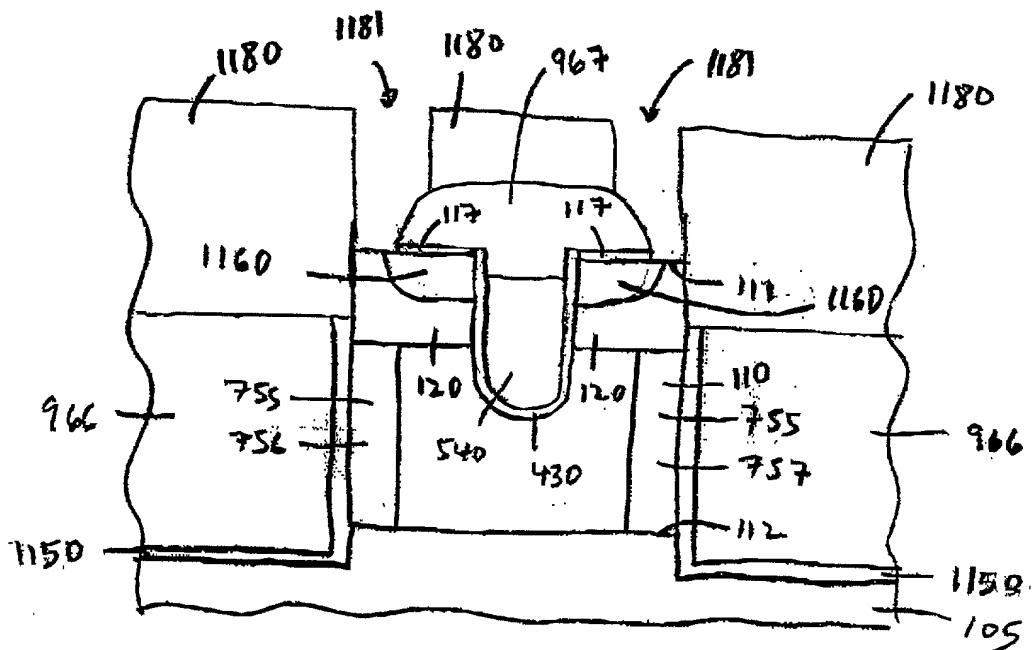
100

FIG. 9



1000

FIG. 10



1100

FIG. 11

000000000000000000000000

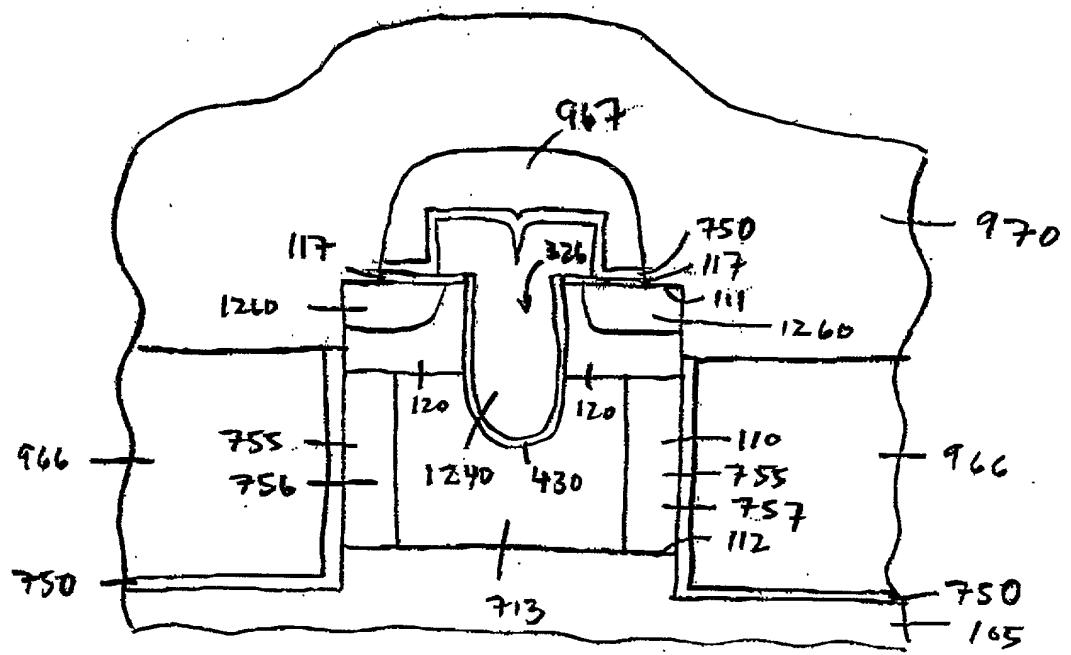


FIG. 12

FIG. 13

1300

1310 Providing a semiconductor layer over a semiconductor substrate



1320 Forming a channel region in the semiconductor layer



1330 Forming a first trench in the semiconductor layer



1340 Forming a control electrode in the trench



1350 Forming a second trench into the semiconductor layer



1360 Forming a charge balancing region in the semiconductor



1370 Forming a heavily doped region in the semiconductor layer



1380 Forming an electrical contact coupled to the heavily doped region



1390 Forming another electrical contact coupled to the semiconductor
substrate